

SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE: 20 --- 200 V

CURRENT:30.0A

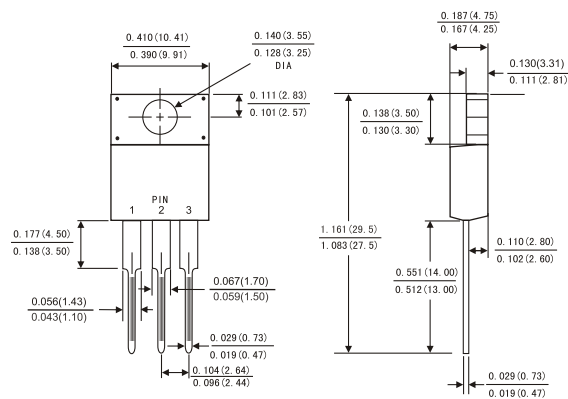
FEATURES

- ◇ Metal-semiconductor junction with guard ring
- ◇ Epitaxial construction
- ◇ Low forward voltage drop,low switching losses
- ◇ High surge capability
- ◇ For use in low voltage,high frequency inverters free wheeling,and polarity protection applications
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case:JEDEC ITO-220AB ,molded plastic
- ◇ Terminals: Axial lead ,solderable per MIL- STD-750,Method 2026
- ◇ Polarity: As marked
- ◇ Weight: 0.08ounces,2.24 grams
- ◇ Mounting position: Any

ITO - 220AB



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		Symbols	SRF 3020CT	SRF 3030CT	SRF 3040CT	SRF 3045CT	SRF 3060CT	SRF 3080CT	SRF 30A0CT	SRF 30150CT	SRF 30200CT	Units
Maximum repetitive peak reverse voltage		VRRM	20	30	40	45	60	80	100	150	200	Volts
Maximum RMS voltage		VRMS	14	21	28	32	42	56	70	105	140	Volts
Maximum DC blocking voltage		VDC	20	30	40	45	60	80	100	150	200	Volts
Maximum average forward rectified current(see Fig.1)	Per leg	I(AV)	15.0 30.0									Amps
	Total device											
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)		IFSM	250.0									Amps
Maximum instantaneous forward voltage at 30.0 A		VF	0.60				0.75	0.85		0.95		Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	Tc =25℃	IR	0.2									mA
	Tc =125℃		30			50						
Typical thermal resistance (Note 2)		RθJC	3.0									℃/W
Operating junction temperature range		TJ	-65 to+150									℃
Storage temperature range		TSTG	-65 to+150									℃

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
3.Thermal resistance junction to ambient

FIG.1-FORWARD CURRENT DERATING CURVE

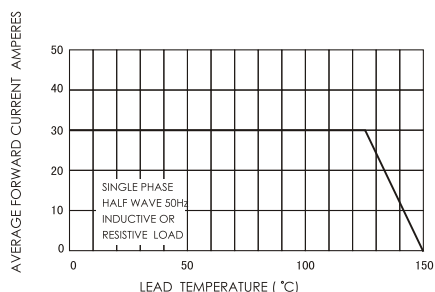


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT PER DIODE

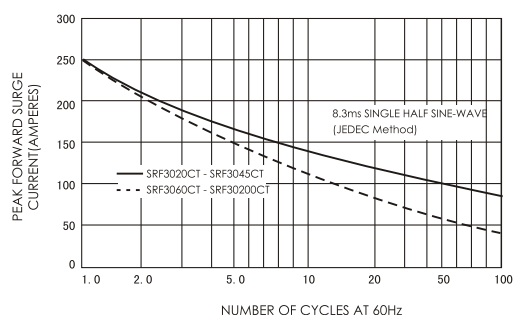


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

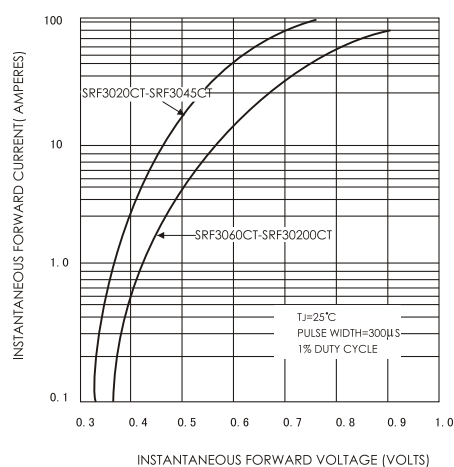


FIG.4-TYPICAL REVERSE CHARACTERISTICS

